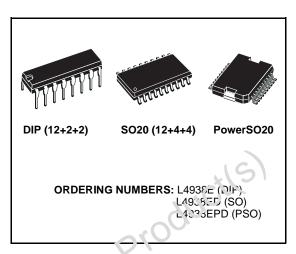


ADVANCED VOLTAGE REGULATOR

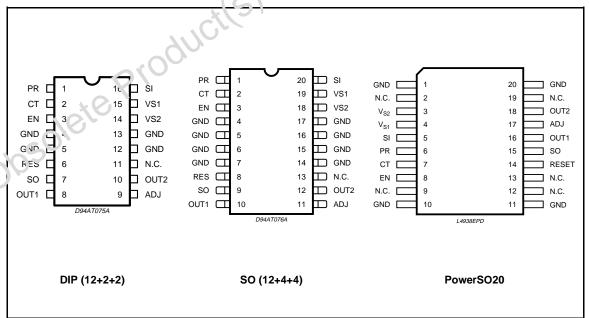
- ENABLE AND SENSE INPUTS (EN, SI) PRO-TECTED AGAINST NEGATIVE TRANSIENTS DOWN TO -5V
- RESET THRESHOLD ADJUSTABLE FROM 3.8 TO 4.7V
- EXTREMELY LOW QUIESCENT CURRENT, 65μA (LESS THAN 90μA) IN STANDBY MODE
- OPERATING DC SUPPLY VOLTAGE RANGE 5V - 28V
- OPERATING TRANSIENT SUPPLY VOLT-AGE UP TO 40V
- HIGH PRECISION STANDBY OUTPUT VOLT-AGE 5V ± 1% WITH 100mA CURRENT CA-PABILITY
- OUTPUT 2 VOLTAGE 5V ± 2% WITH 400mA CURRENT CAPABILITY (ADJ WIRED TO VOUT2)
- OUTPUT 2 VOLTAGE ADJUSTABLE BY EX-TERNAL VOLTAGE DIVIDER
- OUTPUT 2 DISABLE FUNCTION FOR STANDBY MODE



DESCRIPTION

The L4938F, L'EPD is a monolithic integrated dual voltage regulator with two very low dropout outputs and additional functions as power-on reset and input voltage sense. It is designed for upplying the microcomputer controlled systems especially in automotive applications.

PIN CONNECTIONS



February 1999 1/12

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{INDC}	DC Operating Supply Voltage	28	V
V _{INTR}	Transient Operating Supply Voltage (T < 400ms)	-14 to 40	V
Io	Output Current	internally limited	
V _{SI}	Sense Input Voltage (Voltage Forced) (note 2)	-20 to 20	V
I _{SI}	Sense Input Current (Current Forced) (note 2)	±1	mA
V_{EN}	Enable Input Voltage (Voltage Forced) (note 2)	-20 to 20	V
I _{EN}	Sense Input Current (Current Forced) (note 2)	±1	mA
V_{RES} , V_{SO}	Output Voltages	-0.3 to 20	V
I _{RES} , I _{SO}	Output Currents (Output Low)	5	mA
Po	Power Dissipation at T _{amb} = 80°C (note 3) Powerdip 12+2+2	875	mW
T _{stg}	Storage Temperature	-65 to 150	°C
T_j	Operating Junction Temperature	-40 to 150	°C
T _{JSD}	Thermal shutdown junction temperature Output 2 will shut-down typically at Tj 10K lower than output 1	165	ô

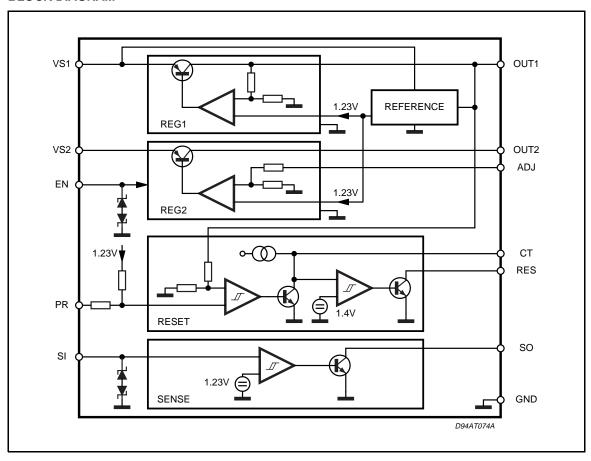
Note 1: The circuit is ESD protected according to MIL-STD-883C

Note 2: Current forced means voltage unlimited but current limited to the specified value

Voltage forced means voltage limited to the specified valueswhile the current is not limited

Note 3: Typical value soldered on a PC board with 8cm² copper ground plane (35mm thick).

BLOCK DIAGRAM



THERMAL DATA

Symbol	Parameter	DIP 12+2+2	SO 12+4+4	PowerSO20	Unit
R _{th j-amb}	Thermal Resistance Junction to ambient	40	50	-	°C/W
R _{th j-case}	Thermal Resistance Junction to case	-	-	<2	°C/W

Note 3: Typical value soldered on a PC board with 8cm² copper ground plane (35mm thick).

PIN FUNCTIONS

PIN (DIP 12+2+2)	PIN (SO 12+4+4)	PIN PowerSO20	Name	Function
14	18	3	VS2	Supply Voltage (400mA Regulator)
15	19	4	VS1	Supply Voltage (100mA Regulator, Reset, Sense)
16	20	5	S1	Sense Input
1	1	6	PR	Reset Theresold Programming
2	2	7	СТ	Reset Delay Capacitor
3	3	8	EN	Enable (low will activate the 400mA regulator)
4, 5, 12, 13	4, 5, 6, 7, 14, 15, 16, 17	1,10,11,20	GND	Ground
6	8	14	RES	Reset Output
7	9	15	SO	Sense Output
8	10	16	OUT 1	100mA Regulator Output
9	11	17	ADJ	Feedback of 400mA Regulator
10	12	18	OUT 2	400mA Regulator Output
11	13	2,9,19	NC	Not Connected

ELECTRICAL CHARACTERISTICS ($V_S = 14V$; $T_j = -40$ to $150^{\circ}C$ unless otherwise specified.)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
OUT 1						
V _{O1}	Supply Output Voltage	V _S = 6 to 28V; I _{O1} = 400μA to 100mA	4.9	5	5.1	V
		$T_i \le 125^{\circ}C$; $I_{O1} = 50$ to $400\mu A$	4.8	5	5.2	V
V_{DP1}	Dropoutput Voltage 1	$I_{OUT1} = 10mA$		0.1	0.2	V
		$I_{OUT1} = 100 \text{mA}; V_S = 4.8 \text{V}$		0.2	0.4	V
V _{OL01}	Load Regulation 1	I _{OUT1} = 1 to 100mA (after regulation setting)			25	mV
V_{LIM1}	Current Limit 1	VOUT1 = 0.8 to 4.5V	100	200	400	mA
I _{QSB}	Quiescent Current in Standby Mode	$I_{EN} \ge 2.4V$ (output 2 disabled) $I_{O1} = 0.1 \text{mA}$; $V_{SI} > 1.3V$		65	90	μΑ
		$T_J < 85^{\circ}C; R_{PR} = 0$		75		μΑ
OUT 2						
V _{O2}	Output Voltage 2 ADJ connected to OUT 2	Enable = LOW; $V_S = 6$ to 28V; $I_{02} = 5$ to 400mA	4.9		5.1	V
V _{DP2}	Dropoutput Voltage 2	I _{OUT2} = 100mA		0.2	0.3	V
		$I_{OUT2} = 400 \text{mA}; V_S = 4.8 \text{V}$		0.3	0.6	V
V _{OL02}	Load Regulation 2	I _{OUT1} = 5 to 400mA (after regulation setting)			50	mV
R _{ADJ}	Adjust Input Resistance		60	100	150	mΑ
I _{LIM2}	Current Limit 2	V02 = 0.8 to 4.5V	450	650	1300	mΑ
ΙQ	Quiescent Current	$I_{OUT1} = 100 \text{mA}; I_{OUT2} = 400 \text{mA}$			20	mΑ
OUT1, OU	Т 2					
V _{OLi 1,2}	Line Regulation	$V_S = 6$ to 28V; $I_{O1} = 1$ mA, $I_{O2} = 5$ mA, (after regulation setting)			20	mV

ELECTRICAL CHARACTERISTICS (Continued)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
ENABLE II	NPUT					
V _{ENL}	Enable Input Low Voltage (Output 2 Active)		-20		1	V
V_{ENH}	Enable Input High Voltage		1.4		20	V
V_{ENhyst}	Enable Hysteresis		20	30	60	mV
I _{EN LOW}	Enable Input Current Low	$V_{EN} = 0$	-20	-8	-3	μΑ
I _{EN HIGH}	Enable Input Current High	$V_{EN} = 1.1 \text{ to 7V; } T_J < 130^{\circ}\text{C;}$	-1	0	1	μΑ
		V _{EN} = 1.1 to 7V; T _J = 130 to 150°C;	-10	0	10	μΑ
RESET CII	RCUIT					
V _{RT}	Reset Theresold Voltage	R _{PR} = ∞	4.5	V _{O1} -0.3	V _{O1} -0.2	V
	(note4)	$R_{PR} = 0$	3.65	3.8	3.95	V
V_{RTH}	Reset Theresold Hysteresis	R _{PR} = ∞	30	60	120	mV
t _{RD min}	Reset Pulse Delay	$C_{RES} = 47 nF; t_r \le 30 \mu s; (note 5)$	40	60	100	ms
t _{RD nom}	Reset Pulse Delay	C _{RES} = 47nF; (note 6)	60	100	140	ms
t _{RR}	Reset Reaction Time	C _{RES} = 47nF	10	50	150	μs
I _{CT}	Pull Down Capability of the Discharge circuit	Vout1 < Vrt	3	6	15	mA
Ict	Charge Current	Vout1 > Vrt	-1.3	-1	0.7	μΑ
V_{RESL}	Reset Output Low Voltage	Rres = $10K\Omega$ to VouT1 VouT1 $\geq 1.5V$			0.4	V
V_{RESH}	Reset Output High Leakage current	V _{RES} = 5V			1	μΑ
SENSE CO	OMPARATOR					
V _{SI}	Functional Range		-20		20	V
V _{SIT}	Sense Threshold Voltage	Falling Edge; T _J <130°C	1.08	1.16	1.24	V
		Falling Edge; T _J <130 to 150°C	1.05	1.16	1.29	V
V _{SITH}	Sense Threshold Hysteresis		10	30	60	mV
V _{SOL}	Sense Output Low Voltage	$V_{SI} \le 1.05V; R_{SO} = 10K\Omega$ connected to 5V; $V_S \ge 5V$			0.4	V
I _{SOH}	Sense Output Leakage	Vso = 5V; Vsı ≥ 1.5V			1	μΑ
I _{SI HIGH}	Sense Input Current High	Vsi = 1.1 to 7V; T _J <130°C	-1	0	1	μΑ
		V _{SI} = 1.1 to 7V; T _J <130 to 150°C	-10	0	10	μA
I _{SI LOW}	Sense Input Current Low	Vsi = 0V	-20	-8	-3	μΑ

Note:

- 4) The reset threshold can be programmed continuously from typ 3.8V to 4.7V by changing a value of an external resistor from pin PR to GN
- 5) This is a minimum reset time according to the hysteresis of the comparator. Delay time starts with Vout1 exceeding VRT
- 6) This is the nominal reset time depending on the discharging limit of C_T (saturation voltage) and theupper threshold of the timer comparator. Delay time starts with Vout1 exceeding VRT
- 7) The leakage of C_T must be less than 0.5mA (2V). If an external resistor between C_T and Vou_{T1} is applied, the leakage current may be increased. The external resistor should have more than $30K\Omega$. for stability: $Cs \ge 1\mu F$, $C01 \ge 10\mu F$, $C02 \ge 10\mu F$, $ESR \le 5\Omega$ (designed target) For details see application note.
- 8) For transients exceeding 20V or -20V external protection is required at the Pins SI and EN as shown at Pin EN. The protection proposed will provide proper function for transients in the range of ± 200 V. If the zener diode is omitted the external resistor should be raised to 200K Ω to limit the current to 1mA. Without the zener diode, the function 20V or -20V can not be guaranteed.

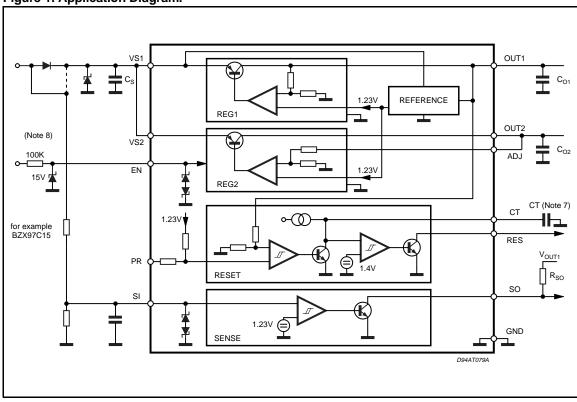


Figure 1. Application Diagram.

FUNCTIONAL DESCRIPTION

The L4938E/ED/EPD is a monolithic integrated dual voltage regulator, based on the STM modulator voltage regulator approach. Several outstanding features and auxiliary functions are implemented to meet the requirements of supplying microprocessor systems in automotive applications. Nevertheless, it is suitable also in other applications where two stabilized voltages are required. The modular approach of this device allows to get easly also other features and functions when required.

Standby Regulator

The standby regulator uses an Isolated collector Vertical PNP transistor as a regulating element. With this structure very low dropout volotage at currents up to 100mA is obtained. The dropout operation of the standby regulator is maintained down to 3V input supply voltage. The output voltage is regulated up to the transient input supply voltage of 40V. With this feature no functional interruption due to overvoltage pulses is generated.

In the standby mode when the output 2 is disabled, the current consumption of the device (quiescent current) is less than $90\mu A$ (14V supply voltage).

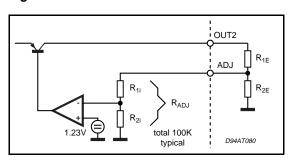
To reduce the quiescent current peak in the undervoltage region and to improve the transient response in this region, the dropout voltage is controlled. A second regulation path will keep the output voltage without load below 5.5V even at high temperatures.

Output 2 Voltage

The output 2 regulator uses the same output structure as the standby regulator but rated for the output current of 400mA. The output voltage is internally fixed to 5V if ADJ is connected to VOUT2.

The output 2 regulator can be switches OFF via the enable input.

Figure 2.



4

Connecting a resistor divider R_{1E} , R_{2E} to the ADJ, OUT2 pin the output voltage 2 can be programmed to the value of

$$V_{OUT2} = V_{OUT1} \left(1 + \frac{R_{1E}(R_{2E} + R_{ADJ})}{R_{2E} \cdot R_{ADJ}} \right)$$

with R_{ADJ} = 60K to 150K and V_{OUT1} = 4.95 to 5.05V.

For an exact calculation the temperature coefficient (Tc -2000pprm) of the internal resistor (R_{ADJ}) must be taken into account. Pin ADJ in this mode should not have a capacitive burden because this would reduce the phase margin of the regulator loop.

Reset circuit

The reset circuit supervises the standby output voltage. The reset output (RES) is defined from $V_{OUT} \ge 1V$.

Even if V_S is lacking, the reset generator is supplied by the output voltage V_{OUT1} .

The reset threshold of 4.7V is defined with the internal reference voltage (note 9) and standby output divider, when pin PR is left open. The reset threshold voltage can be programmed in the range from 3.8V to 4.7V by connecting an external resistor from pin PR to GND.

The value of the programming resistor R_{PR} can be calculated with:

$$R_{PR} = \frac{22K}{\frac{4.7K}{V_{PT}}} - 92.9K, 3.8V \le V_{RT} \le 4.7V$$

The reset pulse delay time t_{RD} , is defined with the charge time of an external capacitor C_T :

$$t_{RDmin} = \frac{C_T \cdot 0.6V}{1\mu A} \text{ (note 5)}$$

$$t_{RDnom} = \frac{C_T \cdot 1.4V}{1\mu A} \text{ (note 6)}$$

The reaction time of the reset circuit originates from the noise immunity. Standby output voltage drops below the reset threshold only a bit longer than the reaction time results in a shorter reset delay time. The nominal reset delay time will be generated for standby output voltage drops longer

than approximately 50µs.

The minimum rset time is generated if reset condition only occures for a short time triggering a reset pulse but not completely discharging C_T . The reset can be related to output2 on request. If higher charge currents for the reset capacitor are required a resistors from Pin C_T to OUT1, may be used to increase the current. We recommended the use of $10 \text{K}\Omega$ to 5 V as an output pull up.

Sense Comparator

The sense comparator compares an input signal with an internal voltage reference of typical 1.23V. The use of an external voltage divider makes this comparator very flexible in the application. It can be used to supervise the input voltage either before or after the protection diode and to give additional information to the microprocessor like low voltage warnings. We recommended the use of $10 \mathrm{K}\Omega$ to 5V as an output pull up.

Note 9:

The reference is alternatively supplied from V_S or V_{OUT1} . If one supply is present, the reference is operating.

Thermal Protection

Both outputs are provided with an overtemperature shut down regulation power dissipation down to uncritical values.

Output 2 will shut down approximately 10K before output 1.

Under normal conditions shut down of output 2 will allow the chip to cool down again. Thus output 1 will be unaffected.

The thermal shut down reduces the output voltages until power dissipation and the flow of thermal energy out of the chip balance.

Transient Sensitivity

In proper operation ($V_{OUT} > 4.5V$) the reference is supplied by V_{OUT1} thus reducing sensitivity to input transients.

Precise Data will be issued as soon as samples are available.

Figure 3. Reset Generator

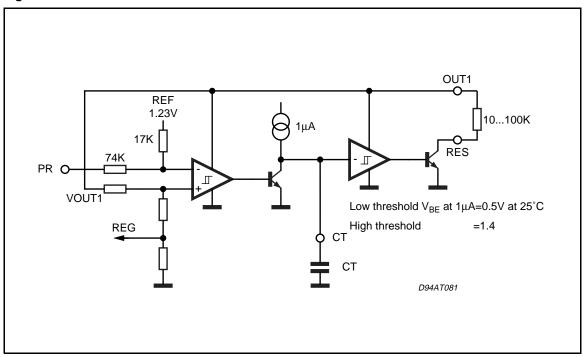
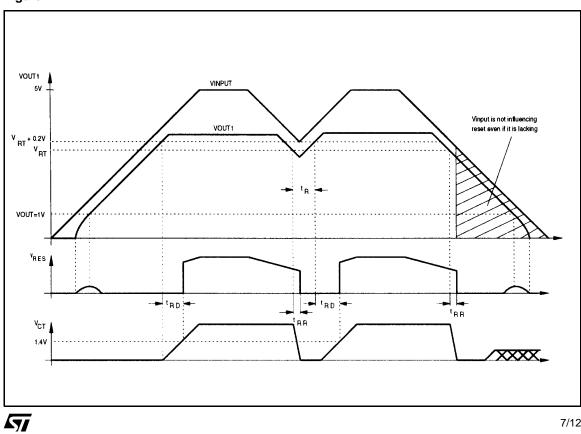


Figure 4:

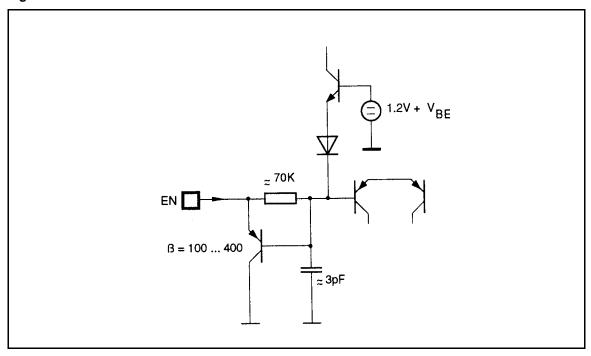


INPUT PROTECTION

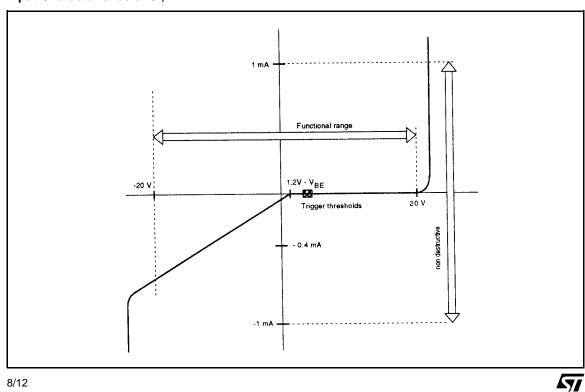
The Inputs Enable (EN) and sense in(SI) are pro-

tected against negative transients. Figure 5 is showing the simplified schematic

Figure 5.

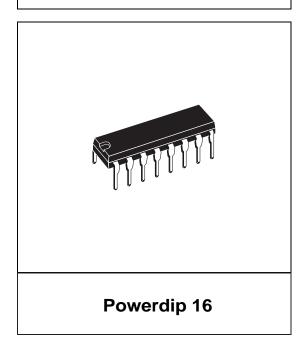


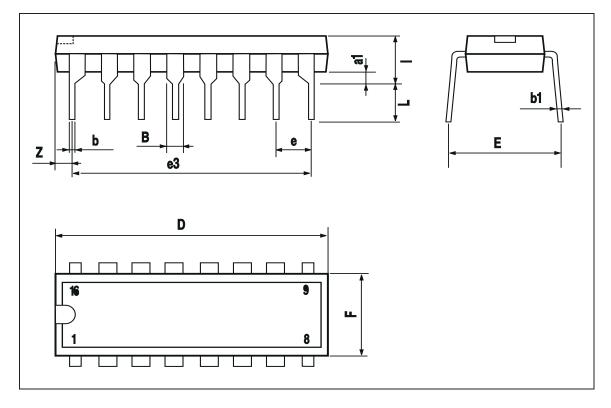
Input Characteristics of SI, EN:



DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.85		1.40	0.033		0.055
b		0.50			0.020	
b1	0.38		0.50	0.015		0.020
D			20.0			0.787
E		8.80			0.346	
е		2.54			0.100	
e3		17.78			0.700	
F			7.10			0.280
I			5.10			0.201
L		3.30			0.130	
Z			1.27			0.050

OUTLINE AND MECHANICAL DATA

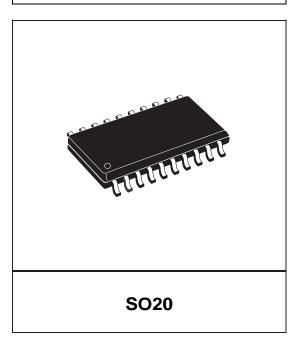


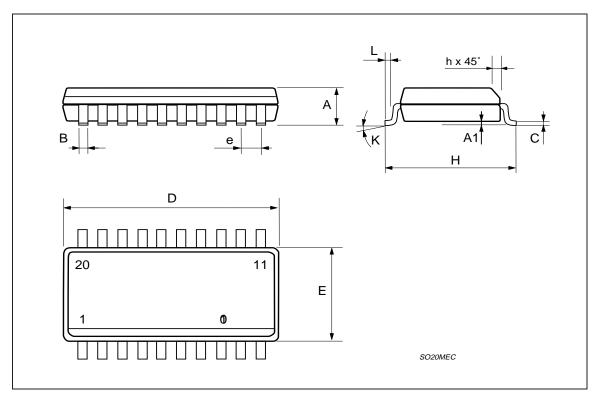


L4938E - L4938EPD - L4938EPD

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	MIN. TYP.		
Α	2.35		2.65	0.093		0.104	
A1	0.1		0.3	0.004		0.012	
В	0.33		0.51	0.013		0.020	
С	0.23		0.32	0.009		0.013	
D	12.6		13	0.496		0.512	
Е	7.4		7.6	0.291		0.299	
е		1.27			0.050		
Н	10		10.65	0.394		0.419	
h	0.25		0.75	0.010		0.030	
L	0.4		1.27	0.016		0.050	
К	0° (min.)8° (max.)						

OUTLINE AND MECHANICAL DATA

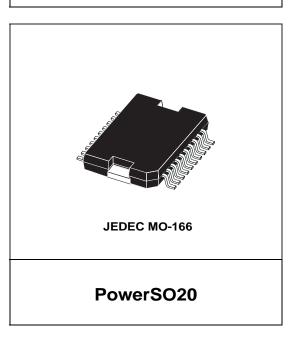


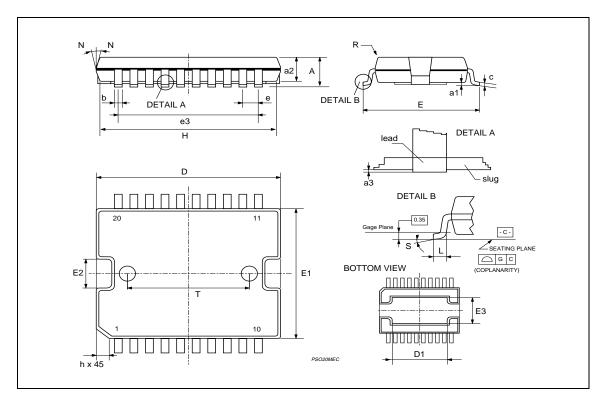


DIM.		mm			inch		
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			3.6			0.142	
a1	0.1		0.3	0.004		0.012	
a2			3.3			0.130	
a3	0		0.1	0.000		0.004	
b	0.4		0.53	0.016		0.021	
С	0.23		0.32	0.009		0.013	
D (1)	15.8		16	0.622		0.630	
D1	9.4		9.8	0.370		0.386	
Е	13.9		14.5	0.547		0.570	
е		1.27			0.050		
e3		11.43			0.450		
E1 (1)	10.9		11.1	0.429		0.437	
E2			2.9			0.114	
E3	5.8		6.2	0.228		0.244	
G	0		0.1	0.000		0.004	
Н	15.5		15.9	0.610		0.626	
h			1.1			0.043	
L	0.8		1.1	0.031		0.043	
N	10° (max.)						
S			8° (n	max.)			
Т		10			0.394		

(1) "D and F" do not include mold flash or protrusions. - Mold flash or protrusions shall not exceed 0.15 mm (0.006"). - Critical dimensions: "E", "G" and "a3"

OUTLINE AND MECHANICAL DATA





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